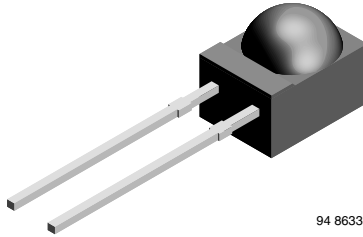


## Silicon PIN Photodiode



### FEATURES

- Package type: leaded
- Package form: side view
- Dimensions (in mm): 4.5 x 5 x 6
- Radiant sensitive area (in mm<sup>2</sup>): 7.5
- High radiant sensitivity
- Daylight blocking filter matched with 940 nm emitters
- Fast response times
- Angle of half sensitivity:  $\phi = \pm 60^\circ$
- Compliant to RoHS Directive 2002/95/EC and in accordance to WEEE 2002/96/EC



### Note

\*\* Please see document "Vishay Material Category Policy":  
[www.vishay.com/doc?99902](http://www.vishay.com/doc?99902)

### APPLICATIONS

- High speed detector for infrared radiation
- Infrared remote control and free air data transmission systems, e.g. in combination with TSALxxxx series IR emitters

### DESCRIPTION

BPV22F is a PIN photodiode with high speed and high radiant sensitivity in a black, plastic package with side view lens and daylight blocking filter. Filter bandwidth is matched with 900 nm to 950 nm IR emitters. The lens achieves 80 % of sensitivity improvement in comparison with flat package.

| PRODUCT SUMMARY |                      |              |                      |
|-----------------|----------------------|--------------|----------------------|
| COMPONENT       | $I_{ra}$ ( $\mu A$ ) | $\phi$ (deg) | $\lambda_{0.5}$ (nm) |
| BPV22F          | 80                   | $\pm 60$     | 870 to 1050          |

### Note

- Test condition see table "Basic Characteristics"

| ORDERING INFORMATION |           |                              |              |
|----------------------|-----------|------------------------------|--------------|
| ORDERING CODE        | PACKAGING | REMARKS                      | PACKAGE FORM |
| BPV22F               | Bulk      | MOQ: 4000 pcs, 4000 pcs/bulk | Side view    |

### Note

- MOQ: minimum order quantity

| ABSOLUTE MAXIMUM RATINGS ( $T_{amb} = 25^\circ C$ , unless otherwise specified) |  |            |               |            |
|---|--|------------|---------------|------------|
| PARAMETER   | TEST CONDITION                               | SYMBOL     | VALUE         | UNIT       |
| Reverse voltage   |  | $V_R$      | 60            | V          |
| Power dissipation   | $T_{amb} \leq 25^\circ C$                    | $P_V$      | 215           | mW         |
| Junction temperature  |  | $T_j$      | 100           | $^\circ C$ |
| Operating temperature range   |  | $T_{amb}$  | - 40 to + 100 | $^\circ C$ |
| Storage temperature range   |  | $T_{stg}$  | - 40 to + 100 | $^\circ C$ |
| Soldering temperature   | $t \leq 5$ s                                 | $T_{sd}$   | 260           | $^\circ C$ |
| Thermal resistance junction/ambient   | Connected with Cu wire, 0.14 mm <sup>2</sup> | $R_{thJA}$ | 350           | K/W        |

| <b>BASIC CHARACTERISTICS</b> ( $T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified) |   |                 |      |                     |      |                               |
|---|---|-----------------|------|---------------------|------|-------------------------------|
| PARAMETER   | TEST CONDITION  | SYMBOL          | MIN. | TYP.                | MAX. | UNIT                          |
| Forward voltage   | $I_F = 50\text{ mA}$  | $V_F$           |      | 1                   | 1.3  | V                             |
| Breakdown voltage   | $I_R = 100\text{ }\mu\text{A}$ , $E = 0$                                      | $V_{(BR)}$      | 60   |                     |      | V                             |
| Reverse dark current  | $V_R = 10\text{ V}$ , $E = 0$   | $I_{ro}$        |      | 2                   | 30   | nA                            |
| Diode capacitance   | $V_R = 0\text{ V}$ , $f = 1\text{ MHz}$ , $E = 0$                             | $C_D$           |      | 70                  |      | pF                            |
| Serial resistance   | $V_R = 12\text{ V}$ , $f = 1\text{ MHz}$                                      | $R_S$           |      | 400                 |      | $\Omega$                      |
| Open circuit voltage  | $E_e = 1\text{ mW/cm}^2$ , $\lambda = 950\text{ nm}$                          | $V_o$           |      | 370                 |      | mV                            |
| Temperature coefficient of $V_o$  | $E_e = 1\text{ mW/cm}^2$ , $\lambda = 950\text{ nm}$                          | $TK_{V_o}$      |      | - 2.6               |      | mV/K                          |
| Short circuit current   | $E_e = 1\text{ mW/cm}^2$ , $\lambda = 950\text{ nm}$                          | $I_k$           |      | 75                  |      | $\mu\text{A}$                 |
| Reverse light current   | $E_e = 1\text{ mW/cm}^2$ , $\lambda = 950\text{ nm}$ ,<br>$V_R = 5\text{ V}$  | $I_{ra}$        | 55   | 80                  |      | $\mu\text{A}$                 |
| Temperature coefficient of $I_{ra}$   | $E_e = 1\text{ mW/cm}^2$ , $\lambda = 950\text{ nm}$ ,<br>$V_R = 10\text{ V}$ | $TK_{I_{ra}}$   |      | 0.1                 |      | %/K                           |
| Absolute spectral sensitivity   | $V_R = 5\text{ V}$ , $\lambda = 870\text{ nm}$                                | $s(\lambda)$    |      | 0.35                |      | A/W                           |
|   | $V_R = 5\text{ V}$ , $\lambda = 950\text{ nm}$                                | $s(\lambda)$    |      | 0.6                 |      | A/W                           |
| Angle of half sensitivity   |   | $\phi$          |      | $\pm 60$            |      | deg                           |
| Wavelength of peak sensitivity  |   | $\lambda_p$     |      | 950                 |      | nm                            |
| Range of spectral bandwidth   |   | $\lambda_{0.5}$ |      | 870 to 1050         |      | nm                            |
| Quantum efficiency  | $\lambda = 950\text{ nm}$   | $\eta$          |      | 90                  |      | %                             |
| Noise equivalent power  | $V_R = 10\text{ V}$ , $\lambda = 950\text{ nm}$                               | NEP             |      | $4 \times 10^{-14}$ |      | $\text{W}/\sqrt{\text{Hz}}$   |
| Detectivity   | $V_R = 10\text{ V}$ , $\lambda = 950\text{ nm}$                               | $D^*$           |      | $6 \times 10^{12}$  |      | $\text{cm}\sqrt{\text{Hz/W}}$ |
| Rise time   | $V_R = 10\text{ V}$ , $R_L = 1\text{ k}\Omega$ , $\lambda = 820\text{ nm}$    | $t_r$           |      | 100                 |      | ns                            |
| Fall time   | $V_R = 10\text{ V}$ , $R_L = 1\text{ k}\Omega$ , $\lambda = 820\text{ nm}$    | $t_f$           |      | 100                 |      | ns                            |
| Cut-off frequency   | $V_R = 12\text{ V}$ , $R_L = 1\text{ k}\Omega$ , $\lambda = 870\text{ nm}$    | $f_c$           |      | 4                   |      | MHz                           |
|   | $V_R = 12\text{ V}$ , $R_L = 1\text{ k}\Omega$ , $\lambda = 950\text{ nm}$    | $f_c$           |      | 1                   |      | MHz                           |

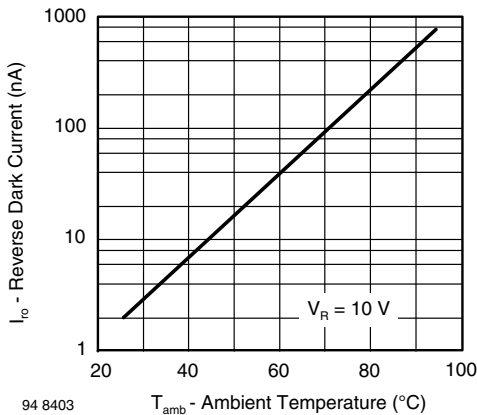
**BASIC CHARACTERISTICS** ( $T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified)


Fig. 1 - Reverse Dark Current vs. Ambient Temperature

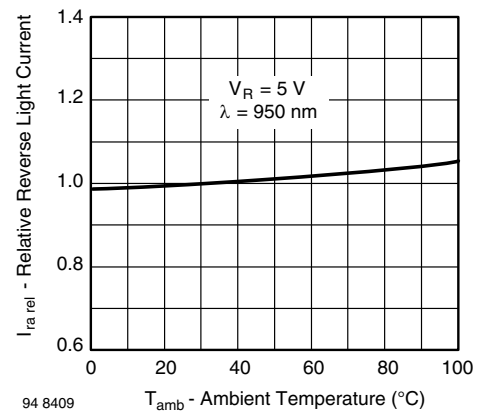


Fig. 2 - Relative Reverse Light Current vs. Ambient Temperature

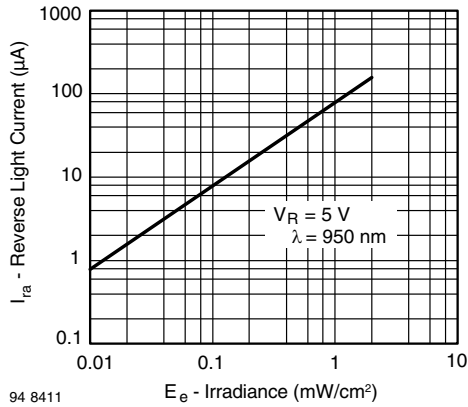


Fig. 3 - Reverse Light Current vs. Irradiance

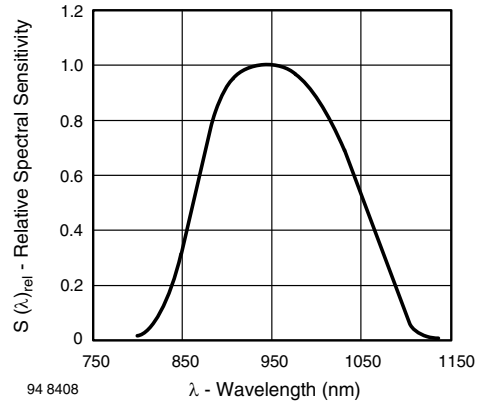


Fig. 6 - Relative Spectral Sensitivity vs. Wavelength

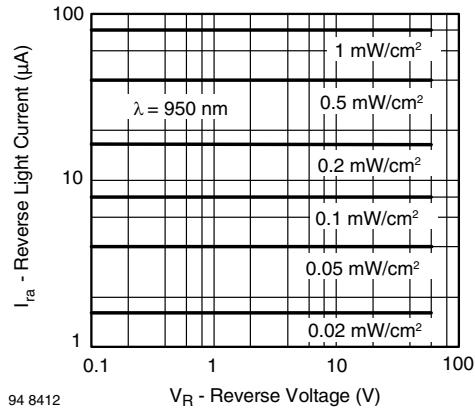


Fig. 4 - Reverse Light Current vs. Reverse Voltage

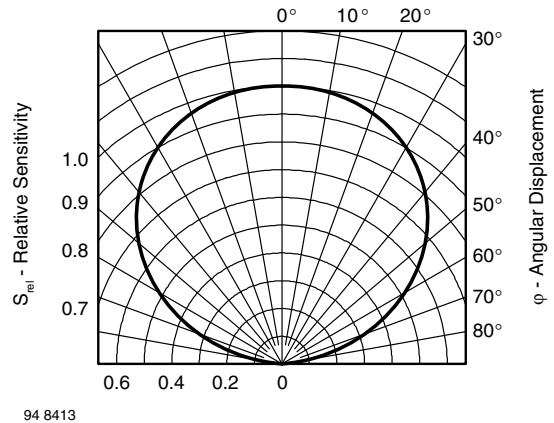


Fig. 7 - Relative Radiant Sensitivity vs. Angular Displacement

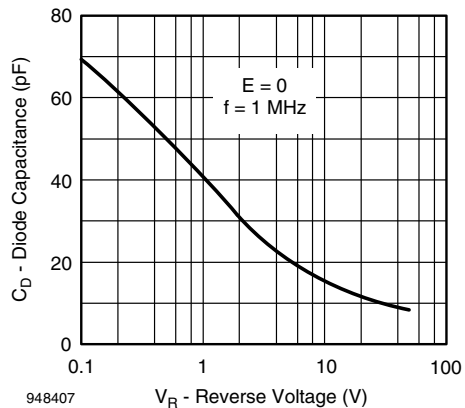
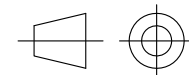
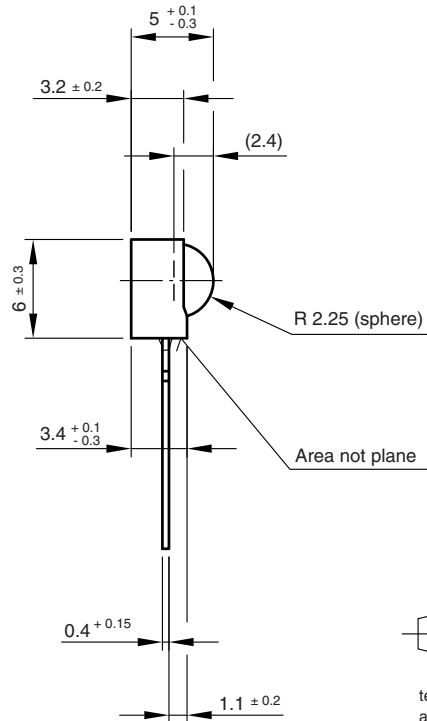
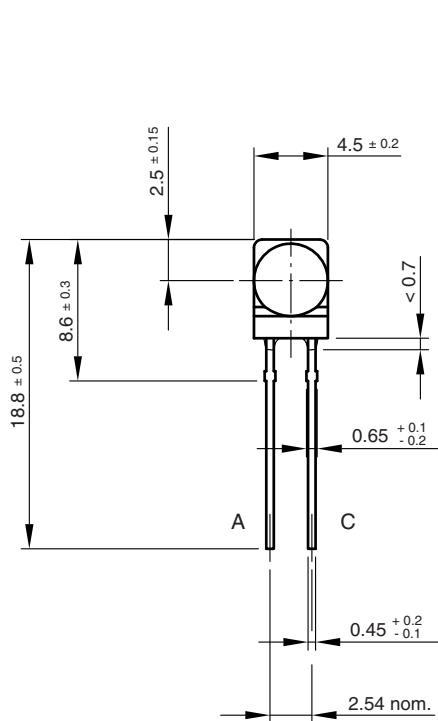


Fig. 5 - Diode Capacitance vs. Reverse Voltage



PACKAGE DIMENSIONS in millimeters



technical drawings according to DIN specifications

Drawing-No.: 6.544-5199.01-4  
Issue: 2; 19.06.01  
95 11475



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